

In the United States Patent and Trademark Office

In re: Kub et al 10/022,364
Serial No.: 09/534,047 (NC 79,684)

Filed: December 20, 2001

For: Method for Transferring Thin Film Layer Material
To a Flexible Substrate Using a Hydrogen Splitting
Technique

#6/Q
7/28/03
MS
Examiner: Foong, Suk San
Art Unit: 2823

March 17, 2003

Amendment

Honorable Commissioner of Patents and Trademarks
Washington, D.C. 20230

Sir:

In response to the office action dated Nov. 21, 2002, please amend claims 1 and 15 as

follows:

1. (Amended) A method for making a thin film device, said method comprising the steps of:

(a) implanting hydrogen to a selected depth within a single crystal semiconducting material substrate to form a hydrogen ion layer so as to divide the single crystal substrate into two distinct portions;

(b) bonding the single crystal semiconducting material substrate to a flexible substrate;

and

(c) splitting the single crystal semiconductor substrate along the implanted ion layer and removing the portion of the substrate, which is on the side of the ion layer away from the flexible substrate, wherein a remaining thin film portion is attached to the flexible substrate.

Q2 06/27/03 YS/LS (Amended) 00A method according to claim 10, wherein the growth substrate comprising
0.5 100.00 DA

**Fax transmission from:**

U.S. Naval Research Laboratory

Associate Counsel Intellectual Property, Code 1008.2

4555 Overlook Avenue, SW

Washington, DC 20375-5325

From: Lawena Brady
Phone: (202) 767-3427
Fax: (202) 404-7380
Date: June 26, 2003

To: Sak-San Foong
PTD
Fax: 703-746-8340
Cover Sheet + 8 Pages

Message:

G
7/1/02
Navy Case 79684 Serial No. 03/534097 10/22/04

Copy of Amendment filed via facsimile on March 17/2003

The information contained in this facsimile may be client confidential, and may also be attorney privileged. The information is intended only for the use of the individual or entity to whom it is addressed. If you are not the intended recipient, you are hereby notified that any use, distribution, or copying of this transmission is prohibited. If you have received this facsimile in error, please notify us immediately by telephone for instructions. Thank you.